Gravitoelectric Conversion Inhibitor-Based Switching

2 February 2026
Simon Edwards
Research Acceleration Initiative

Introduction

Building upon the publication of 17 January 2026, this paper will explore the proposed implementation of miniaturized versions of gravitoelectric (GE) converters for data processing.

Abstract

Rather than use semiconductor transistor-based switching, which generates a substantial amount of heat and requires that two distinct voltages be applied in order to represent either a ‘zero’ or a ‘one’ in the binary system, I propose that a sufficiently miniaturized version of the 17 January 2026 mechanism for gravitoelectric conversion could function within a processor architecture according to the principle of being “on by default” and in which the generator nodes, working by directing magnetism from three polarized atoms made of a ferromagnetic material the magnetism of which converges upon a single point from orientations offset by about 30 degrees of angle for each of the three atoms.

A zero is represented, at least in what could be termed odd-numbered tiers, in such a system, by applying no voltage to the switching mechanism. This causes current to be generated in an inducer on the other side of an insulative barrier. A one is represented by passing current through a paramagnetic atom which is also oriented toward the point of convergence of the three nano- scale permanent magnets. When current is passed through the paramagnetic node, it projects magnetism from a fourth source, disrupting GE conversion as described conceptually in 17 January 2026. In order for current to again begin to be generated by the inducer, all one must do is suspend the flow of current to the paramagnetic node. In such a system, every other switch would handle 0’s as 1’s and 1’s and 0’s, necessitating that states be treated differently in odd and even-numbered tiers, particularly if one eventually wishes to create a computer predicated upon overlapping sets of pathways which can interact with one-another. At minimum, in such a system, there must be an even number of tiers of switches in order to keep the logic of such a system consistent.

This mechanism; like the 17 January 2026 mechanism; depends upon the inducer; which could be as small as a single atom; remaining in constant motion. This requirement becomes more challenging to achieve at the nano-scale as the 17 January 2026 mechanism is large enough that a freely-floating sphere can be filled with a fluid which incorporates magnetism-blocking particles floating in a suspension and motion can be ensured through the application of a modest supplementary force.

Fortunately, the is engineering challenge has already been largely solved as a result of efforts by MIT researchers in 2021, with a good candidate material

having been identified at that time which might be capable of serving this purpose; that material being tetrahedral gallium telluride with embedded free-floating silver ion. In that material, a silver ion naturally tends to oscillate at a high rate of speed about inside of a tetrahedral structure as a consequence of asymmetric Coulomb attraction of the gallium and tellurium components of the structure. Because all of the covalent bonds are “in use” in the structure, the silver ion cannot attach to any of the surrounding materials and remains in motion, alternatingly attracted to the top/bottom (gallium) and the tellurium (on the sides.) The material has the property of being electrically conductive and thermally insulative. It may even be able to absorb and negate a modest amount of thermal energy. Most important is that the inducer, in this case the trapped, free-floating silver ion, remain in motion so that many opportunities are created for spinon formation, leading to electron formation in the GE conversion process.

Conclusion

Advantages of this approach include reduced heat generation, reduced voltage requirements and the ability to operate the device according to the principle of either applying voltage or not applying voltage, as opposed to the application of two discrete voltage levels. The level of voltage required to inhibit the formation of a magnetic vortex associated with gravitoelectric electron conjuration is far less than the amount of current required to achieve induction effects associated with MOSFET or CMOS transistors. Rather than leveraging magnetic induction in which inconsistent magnetic energy is used to produce current on the other side of a barrier, this system uses inconsistent magnetic energy in order to disrupt a smooth and steady gravitoelectric conversion mechanism predicated upon stable, non-alternating magnetic fields. With enough refinement, precision quantities of voltage could be generated with the mechanisms by supplying an amount of current to the disruptor material (most likely a loop of copper,) which is less than what is required to entirely disrupt the gravitoelectric conversion but is enough to introduce an inefficiency or periodic suspension of the generation of the current.

In such a mode of operation, as 90% strength impulse would represented by a 10% strength pulse at the next tier of switches as the introduction of current, in such a system, would, it is important to bear in mind, be inhibitive. A 50% strength impulse would produce a chain of 50% strength impulses, provided that there was enough precision in the control of the voltage (this would be the equivalent of a third option other than zero or one in a ternary computing system.) Such a system, therefore, could be operated on a ternary basis, on a binary basis, or perhaps even an entirely different mode meant to allow for the handling of larger numbers. Whether or not binary, ternary or, perhaps some greater number of base values is appropriate may vary depend upon the application. This system may have as one of its advantages the ability to change the mode of operation of the processor from binary to ternary to quaternary depending upon the type of computation being performed without having to change the physical structure of the processor.